

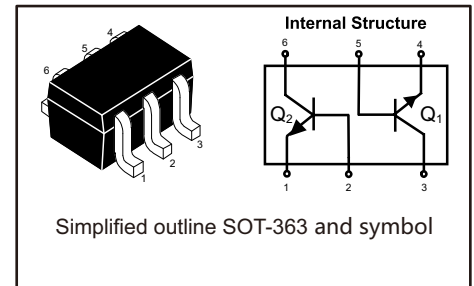
**MMBT3904WH**  
**NPN TRANSISTOR**

**FEATURES**

- As complementary type, the NPN transistor MMBT3906WH is Recommended
- Epitaxial planar die construction

**PINNING**

| PIN   | DESCRIPTION |
|-------|-------------|
| 1 / 4 | EMITTER     |
| 2 / 5 | BASE        |
| 3 / 6 | COLLECTOR   |



**MAXIMUM RATINGS (Ta=25°C unless otherwise noted)**

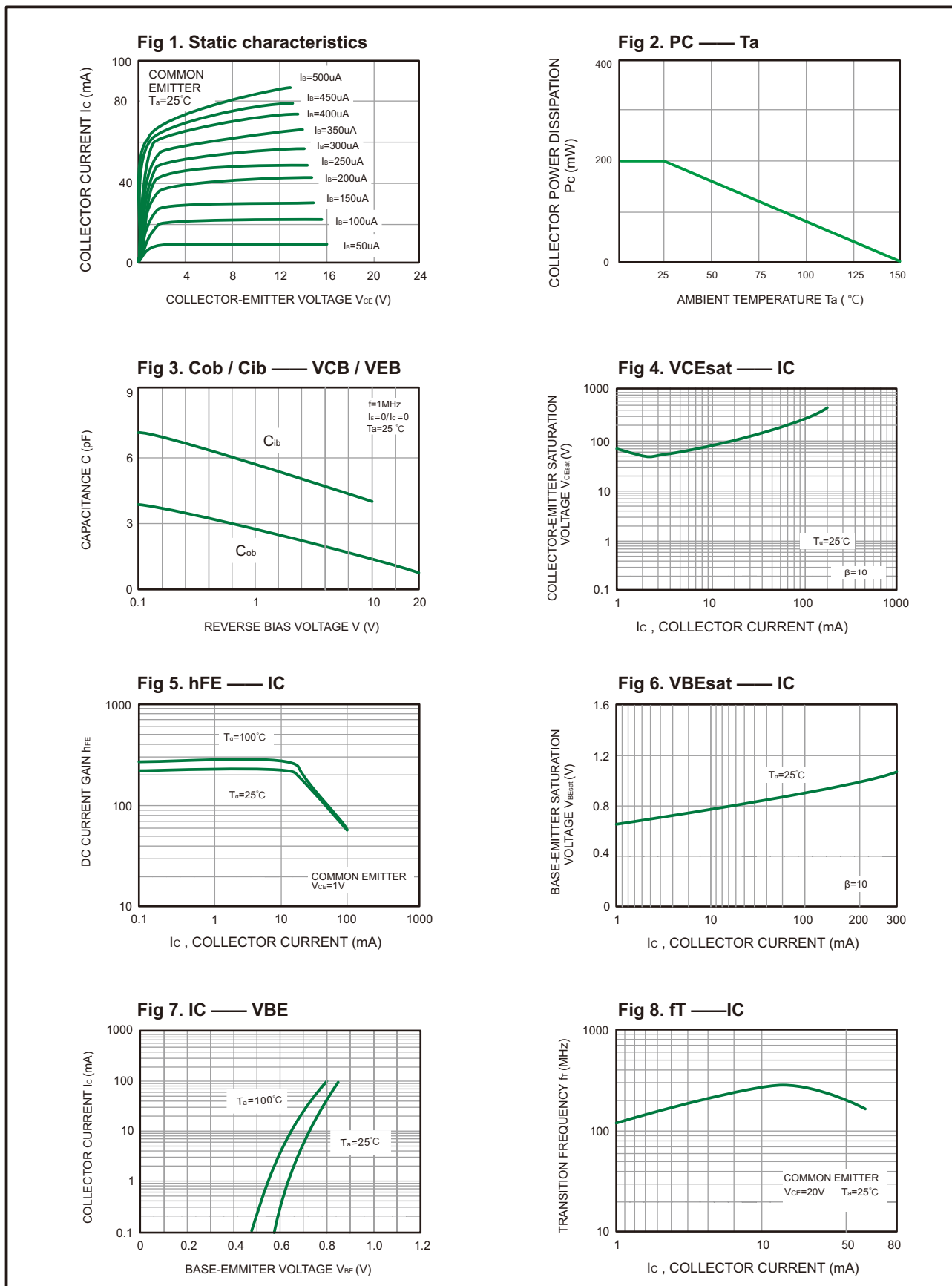
| Parameter  | Symbol          | Value    | Unit |
|--|-----------------|----------|------|
| Collector-Base Voltage                           | $V_{CB0}$       | 60       | V    |
| Collector-Emitter Voltage                        | $V_{CEO}$       | 40       | V    |
| Emitter-Base Voltage                             | $V_{EBO}$       | 6        | V    |
| Collector Current — Continuous                   | $I_C$           | 200      | mA   |
| Collector Power Dissipation                      | $P_C$           | 200      | mW   |
| Thermal Resistance From Junction To Ambient      | $R_{\theta JA}$ | 625      | °C/W |
| Operation Junction and Storage Temperature Range | $T_J, T_{stg}$  | -55~+150 | °C   |

**ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted.)**

| Parameter                            | Symbol        | Test conditions                      | Min | Typ | Max  | Unit |
|--------------------------------------|---------------|--------------------------------------|-----|-----|------|------|
| Collector-base breakdown voltage     | $V_{(BR)CBO}$ | $I_C = 10\mu A, I_E = 0$             | 60  |     |      | V    |
| Collector-emitter breakdown voltage  | $V_{(BR)CEO}$ | $I_C = 1\text{ mA}, I_B = 0$         | 40  |     |      | V    |
| Emitter-base breakdown voltage       | $V_{(BR)EBO}$ | $I_E = 10\mu A, I_C = 0$             | 6   |     |      | V    |
| Collector cut-off current            | $I_{CEX}$     | $V_{CE} = 30V, V_{EB} = 3V$          |     |     | 50   | nA   |
| Collector cut-off current            | $I_{CBO}$     | $V_{CB} = 60V, I_E = 0$              |     |     | 100  | nA   |
| Emitter cut-off current              | $I_{EBO}$     | $V_{EB} = 5V, I_C = 0$               |     |     | 100  | nA   |
| DC current gain                      | $h_{FE(1)}$   | $V_{CE} = 1V, I_C = 10mA$            | 100 |     | 300  |      |
|                                      | $h_{FE(2)}$   | $V_{CE} = 1V, I_C = 50mA$            | 60  |     |      |      |
|                                      | $h_{FE(3)}$   | $V_{CE} = 1V, I_C = 100mA$           | 30  |     |      |      |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = 50mA, I_B = 5mA$              |     |     | 0.3  | V    |
| Base-emitter saturation voltage      | $V_{BE(sat)}$ | $I_C = 50mA, I_B = 5mA$              |     |     | 0.95 | V    |
| Transition frequency                 | $f_T$         | $V_{CE} = 20V, I_C = 10mA, f=100MHz$ | 300 |     |      | MHz  |
| Delay time                           | $t_d$         | $V_{CC}=3V, V_{BE(off)}=-0.5V$       |     |     | 35   | ns   |
| Rise time                            | $t_r$         | $I_C=10mA, I_{B1}=1mA$               |     |     | 35   | ns   |
| Storage time                         | $t_s$         | $V_{CC} = 3V, I_C = 10mA$            |     |     | 200  | ns   |
| Fall time                            | $t_f$         | $I_{B1} = I_{B2} = 1mA$              |     |     | 50   | ns   |

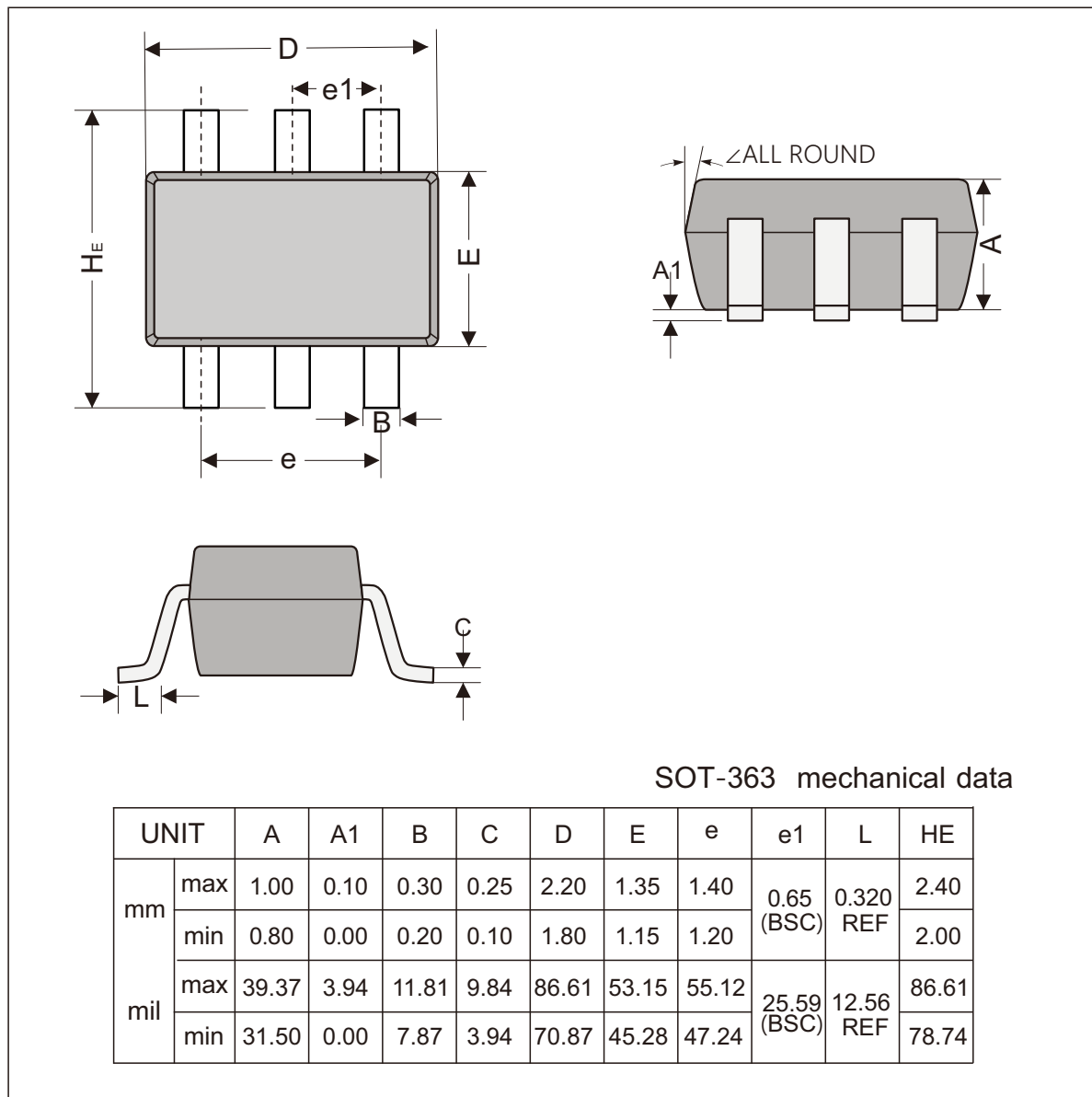


### TYPICAL CHARACTERISTICS

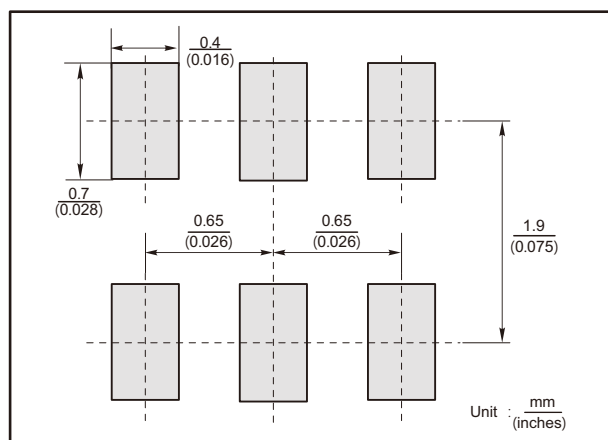




### SOT-363 Package Outline Dimensions



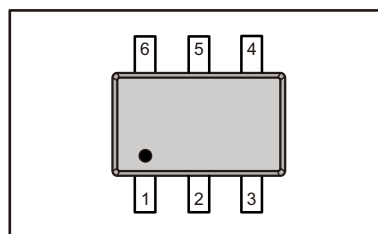
#### The recommended mounting pad size



#### Marking

|             |              |
|-------------|--------------|
| Type number | Marking code |
| MMBT3904WH  | 1AM          |

#### Pin Point





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